

**Inchange Semiconductor**

**Product Specification**

**Silicon NPN Power Transistors**

**2SC3250**

**DESCRIPTION**

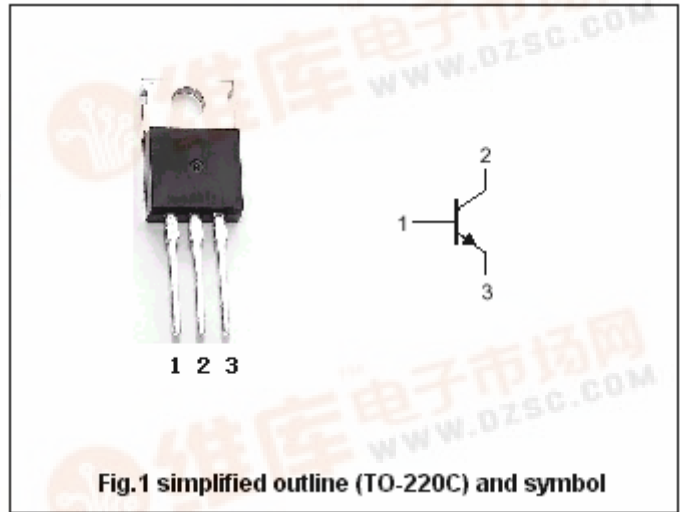
- With TO-220 package
- High  $V_{CE0}$
- Large  $P_C$

**APPLICATIONS**

- For TV video output amplifier applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector; connected to mounting base
3	Emitter



**Absolute maximum ratings ( $T_a=25^{\circ}C$ )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	300	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		0.1	A
$I_{CP}$	Collector current-peak		0.2	A
$P_C$	Collector power dissipation	$T_C=25^{\circ}C$	15	W
$T_j$	Junction temperature		150	$^{\circ}C$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =0.1mA ; I <sub>B</sub> =0	300			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =0.1mA ; I <sub>E</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =0.1mA ; I <sub>C</sub> =0	7			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =5mA			1.5	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =30mA ; V <sub>CE</sub> =10V			1.2	V
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =5mA ; V <sub>CE</sub> =50V	50		250	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =30mA ; V <sub>CE</sub> =10V	30			
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =30V, f=1MHz			5.0	pF
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =-20mA ; V <sub>CB</sub> =30V	70	100		MHz

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PACKAGE OUTLINE

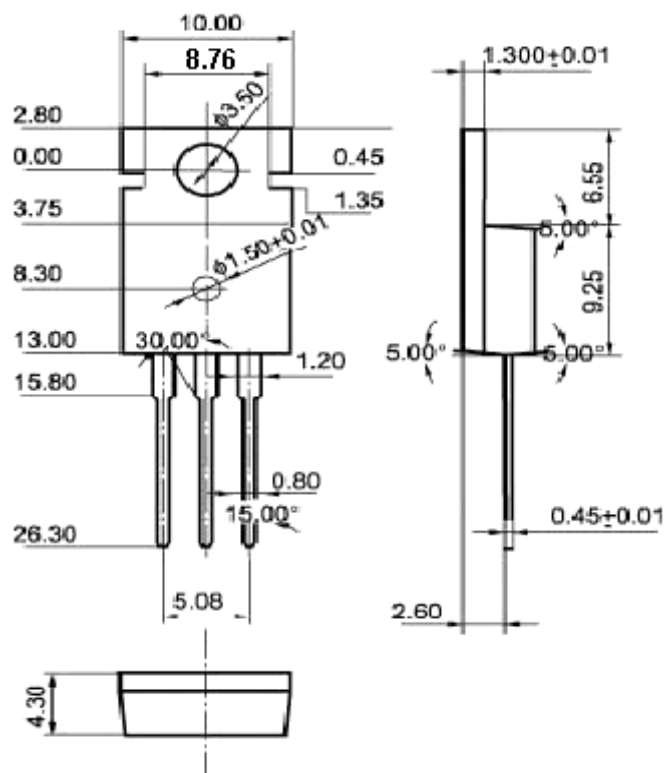


Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)